



# WESTCODE SEMICONDUCTORS



Technical  
Publication

**TN540C**

Issue 3

July 1985

## Converter Grade Capsule Thyristor Type N540C

1400 amperes average: up to 1800 volts  $V_{RRM}$

### Ratings (Maximum values at 125°C $T_j$ unless stated otherwise)

RATING	CONDITIONS	SYMBOL	
Average on-state current	Half sine wave $\left. \begin{array}{l} 55^\circ\text{C heatsink temperature} \\ (\text{double side cooled}) \end{array} \right\}$ $\left. \begin{array}{l} 85^\circ\text{C heatsink temperature} \\ (\text{single side cooled}) \end{array} \right\}$	$I_{T(AV)}$	1400A
R.M.S. on-state current	25°C heatsink temperature, double side cooled	$I_{T(\text{RMS})}$	550A
Continuous on-state current	25°C heatsink temperature, double side cooled	$I_T$	2840A
Peak one-cycle surge (non-repetitive) on state current	10ms duration, 60% $V_{RRM}$ re-applied	$I_{TSM(1)}$	2400A
	10ms duration, $V_R \leq 10$ volts	$I_{TSM(2)}$	20500A
Maximum permissible surge energy	10ms duration, $V_R \leq 10$ volts	$I^2t$	22550A
	3ms duration, $V_R \leq 10$ volts	$I^2t$	2500000A <sup>2</sup> s
Peak forward gate current	Anode positive with respect to cathode	$I_{FGM}$	1890000A <sup>2</sup> s
Peak forward gate voltage	Anode positive with respect to cathode	$V_{FGM}$	20A
Peak reverse gate voltage		$V_{RGM}$	22V
Average gate power		$P_G$	5V
Peak gate power		$P_{GM}$	4W
Rate of rise of off-state voltage	100μs. pulse width	$dv/dt$	120W
Rate of rise of on-state current (repetitive)	To 80% $V_{DRM}$ gate open-circuit	$di/dt(1)$	* 200V/μs
Rate of rise of on-state current (non-repetitive)	$\left. \begin{array}{l} \text{Gate drive 20 volts, 20 ohms with } t_r \leq 1\mu\text{s.} \\ \text{Anode voltage} \leq 80\% V_{DRM} \end{array} \right\}$	$di/dt(2)$	500A/μs
Operating temperature range		$T_{hs}$	1000A/μs
Storage temperature range		$T_{stg}$	-40 + 125°C

### Characteristics (Maximum values at 125°C $T_j$ unless stated otherwise)

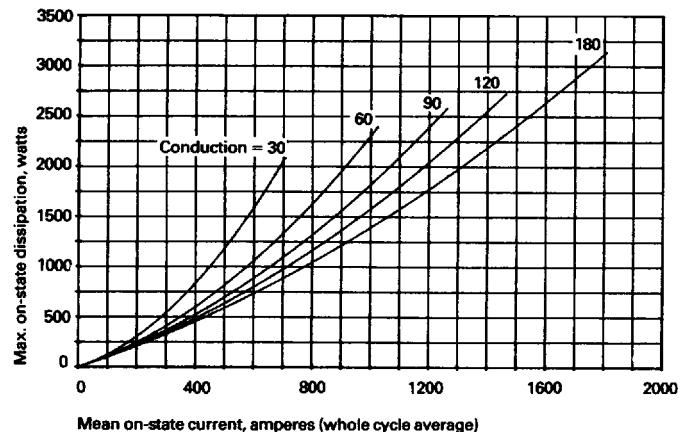
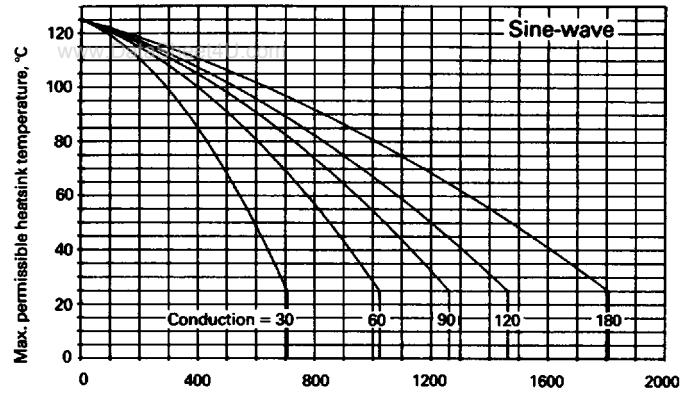
CHARACTERISTIC	CONDITIONS	SYMBOL	
Peak on-state voltage	At 2550 $I_{TM}$	$V_{TM}$	1.41V
Forward conduction threshold voltage		$V_O$	0.965V
Forward conduction slope resistance		$r$	0.174 mΩ
Repetitive peak off-state current	At $V_{DRM}$	$I_{DRM}$	100mA
Repetitive peak reverse current	At $V_{RRM}$	$I_{RRM}$	100mA
Maximum gate current required to fire all devices		$I_{GT}$	300mA
Maximum gate voltage required to fire all devices	$\left. \begin{array}{l} V_A = 6V. I_A = 2A. \text{ at } 25^\circ\text{C } T_j \\ \text{Maximum holding current} \end{array} \right\}$	$V_{GT}$	3V
Maximum holding current		$I_H$	1A
Maximum gate voltage which will not trigger any device		$V_{GD}$	0.25V
Thermal resistance, junction to heatsink, for a device with a maximum forward volt drop characteristic	Double side cooled Single side cooled	$R_{th(j-hs)}$	0.03°C/W 0.06°C/W

VOLTAGE CODE		H02	H04	H06	H08	H10	H12	H14	H16	H18
Repetitive peak voltages		$V_{RRM}$	$V_{DRM}$	200	400	600	800	1000	1200	1400
Non-repetitive peak off-state voltage		$V_{DSM}$		300	500	700	900	1100	1300	1500
Non-repetitive peak reverse blocking voltage		$V_{RSM}$		1600	1800	1700	1900			

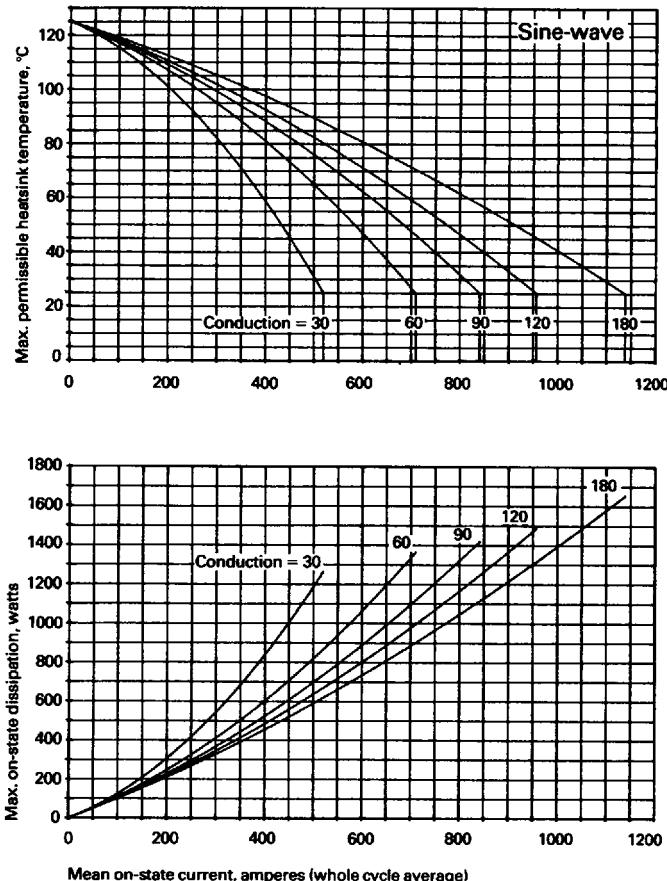
### Ordering Information (Please quote device code as explained below – 8 digits)

N	5	4	0	C	● ● ●	Typical code: N540CH12 = 1200 $V_{RRM}$ 1200 $V_{DRM}$ , 200 V/μs. $dv/dt$ to 80% $V_{DRM}$	www.DataSheet4U.com
					Voltage code (see ratings)		

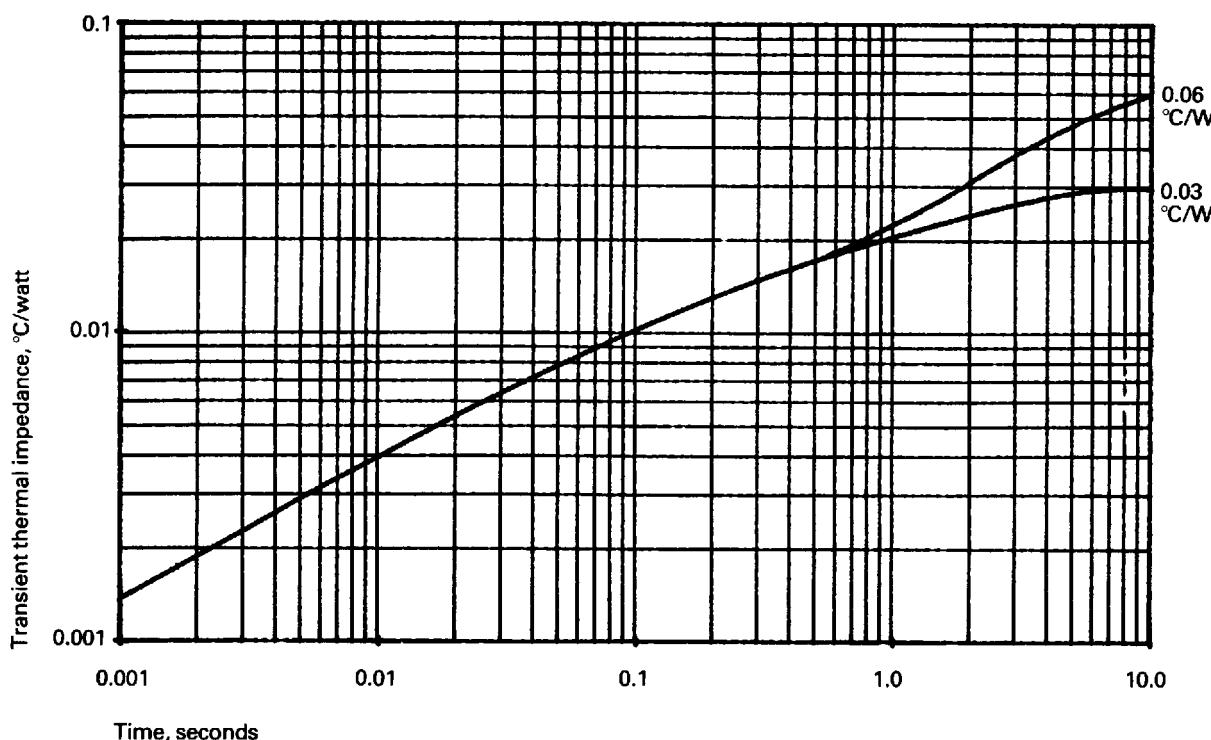
\* Other values of  $dv/dt$  may be available.



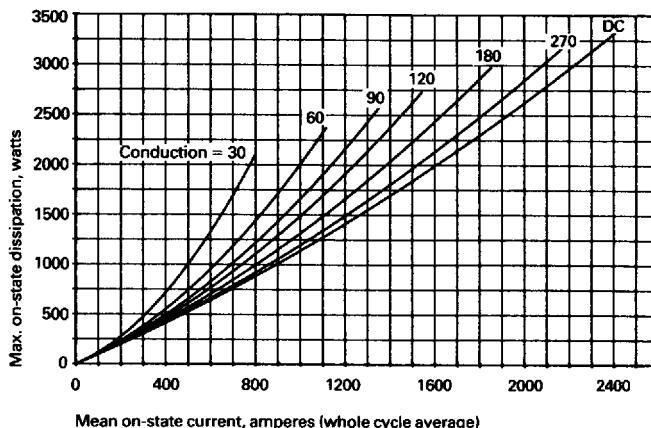
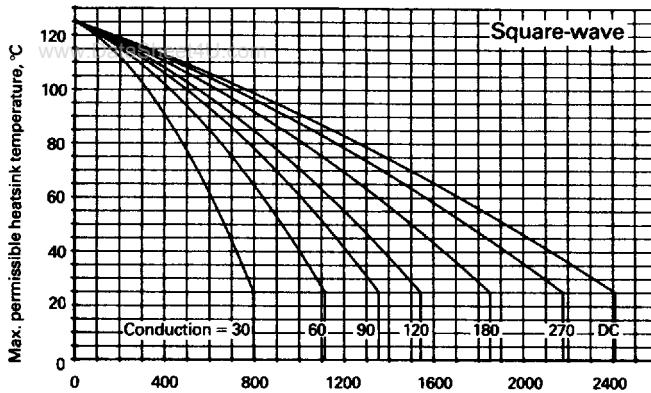
**Figure 1 Dissipation and heatsink temperature v. current (Double side cooled)**



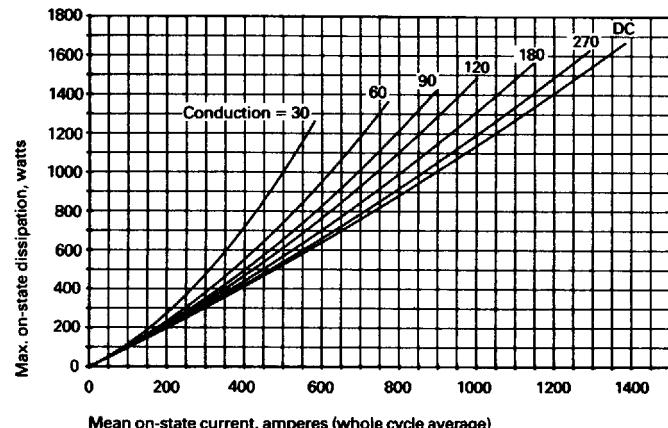
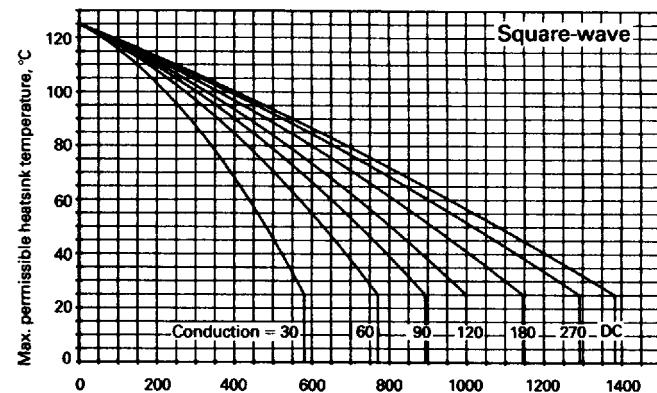
**Figure 2 Dissipation and heatsink temperature v. current (Single side cooled)**



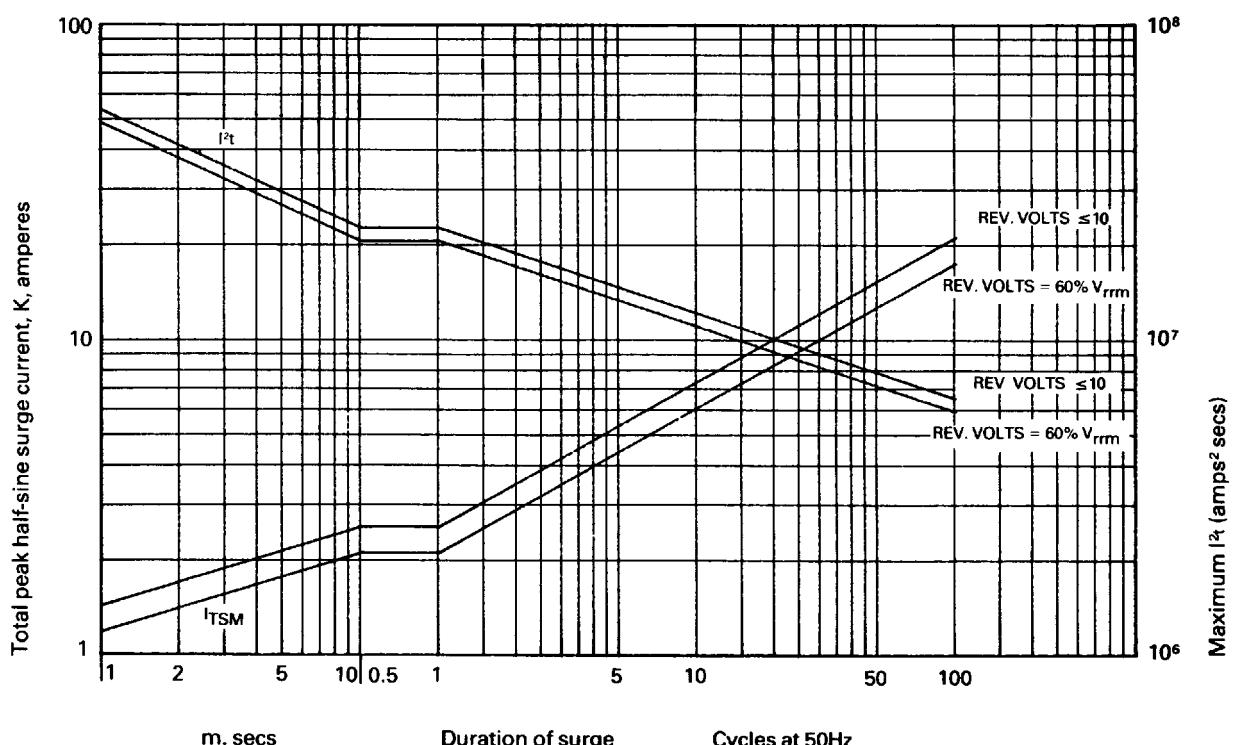
**Figure 3 Junction to heatsink thermal impedance**



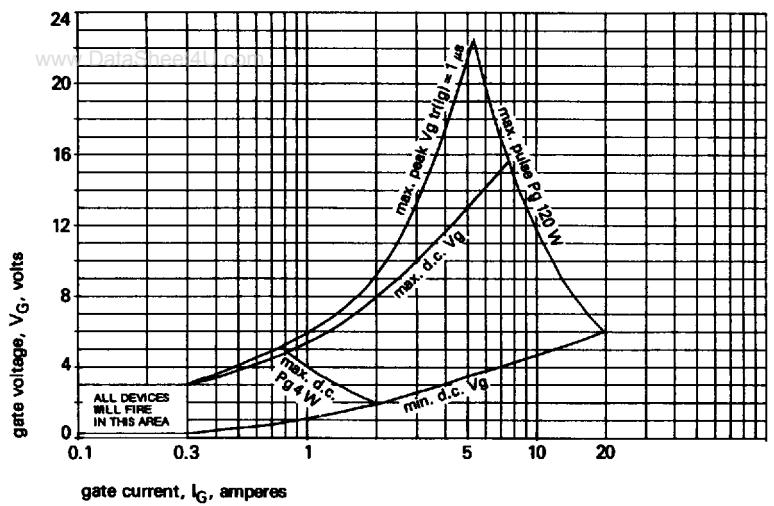
**Figure 4 Dissipation and heatsink temperature v. current (Double side cooled)**



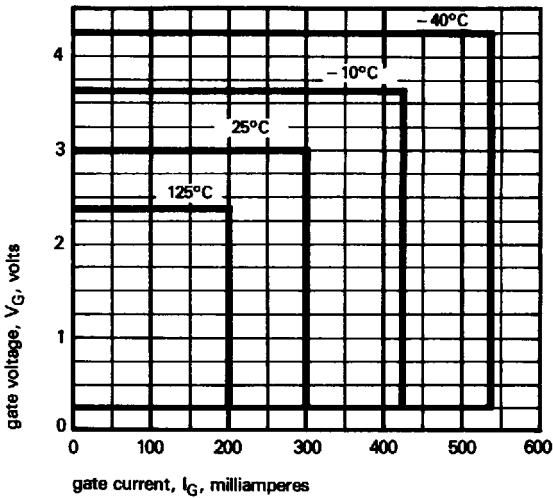
**Figure 5 Dissipation and heatsink temperature v. current (Single side cooled)**



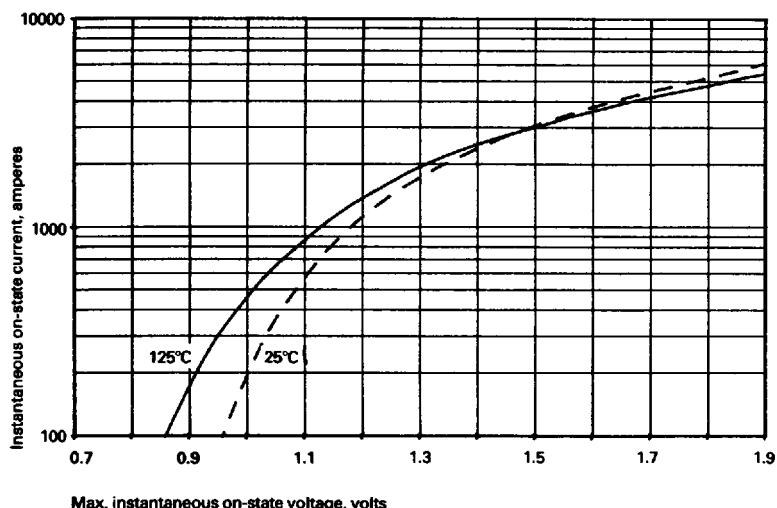
**Figure 6 Max. non-repetitive surge current at initial junction temperature 125°C**  
(gate may temporarily lose control of firing angle)  
Note: This rating must not be interpreted as an intermittent rating



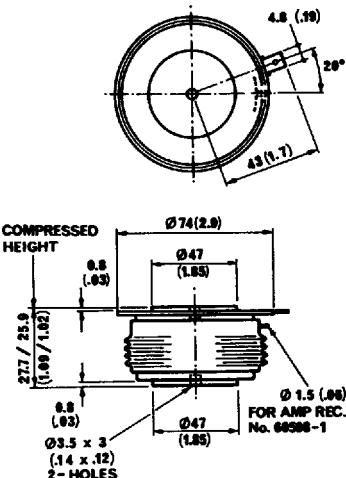
**Figure 7** Gate characteristics at 25°C junction temperature



**Figure 8** Gate triggering characteristics  
Trigger points of all thyristors lie within the areas shown



**Figure 9** Limit on-state characteristic



Dimensions in mm (inches)  
Mounting force: 1900–2600 Kgf  
Weight: 510 grams

In the interest of product improvement, Westcode reserves the right to change specifications at any time without notice.

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